

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,732,236 B2
APPLICATION NO. : 10/598934
DATED : June 8, 2010
INVENTOR(S) : Seiji Nakahata et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, item 54 and col. 1,

In the title:

“III NITRIDE SEMICONDUCTOR DEVICE MANUFACTURING METHOD THEREOF”
should read --III NITRIDE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD
THEREOF--.

Column 11, lines 50 and 51, “10 μm ” should read --10 $\mu\text{m/hr}$ --, and
lines 50 and 52, “300 μm ” should read --300 $\mu\text{m/hr}$ --.

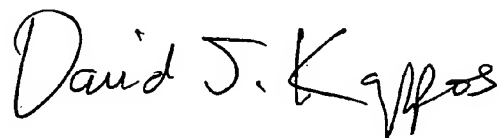
Column 20, lines 48 and 50,
“micro-apertures 2b,” each occurrence, should read --micro-apertures 2s--.

Column 25, line 9, “10 μm ” should read --100 μm --.

Column 54, line 55, “ $\text{Al}_{0.25}\text{Ga}_{0.85}\text{N}$ ” should read -- $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}$ --.

Signed and Sealed this

Ninth Day of November, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large initial 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office